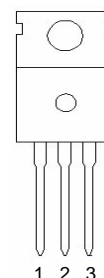


TO-220 Plastic-Encapsulate Transistors

2SC2073 TRANSISTOR (NPN)

TO-220

- 1. BASE
- 2. COLLECTOR
- 3. EMITTER



FEATURES

- Wide safe Operating Area.
- Complementary to 2SA940

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	150	V
V _{CEO}	Collector-Emitter Voltage	150	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	1.5	A
P _C	Collector Power Dissipation	1.5	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E = 0	150			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B = 0	150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100μA, I _C = 0	5			V
Collector cut-off current	I _{CBO}	V _{CB} = 120V, I _E = 0			10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C = 0			10	μA
DC current gain	h _{FE}	V _{CE} = 10V, I _C = 0.5A	40		140	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 0.5A, I _B = 50mA			1.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 10V, I _C = 0.5A	0.65		0.85	V
Transition frequency	f _T	V _{CE} = 10V, I _C = 0.5A		4		MHz
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz		35		pF